

### AM / FM - PLL

### **Description**

The U4285BM is an integrated circuit in BICMOS technology for frequency synthesizers. It performs all the functions of a PLL radio tuning system and is controlled

by an I<sup>2</sup>C bus. The device is designed for all frequency synthesizer applications in radio receivers, as well as RDS ( **R**adio **D**ata **S**ystem ) applications.

#### **Features**

- Reference oscillator up to 15 MHz
- Two programmable 16 bit dividers adjustable from 2 to 65535
- Fine tuning steps:

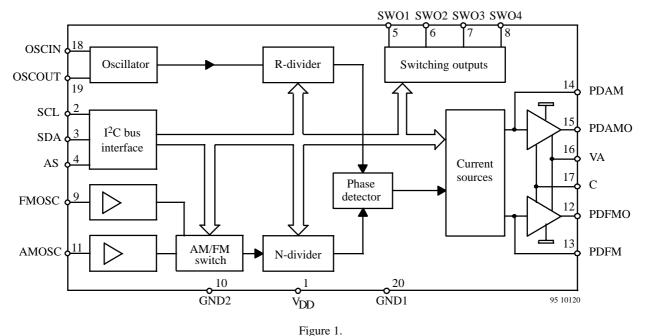
 $AM \ge 1 \text{ kHz}$  $FM \ge 2 \text{ kHz}$ 

- 4 programmable switching outputs (open drain up to 15 V)
- Few external component required due to integrated loop-push-pull stage for AM/FM
- High signal/ noise ratio

### **Ordering Information**

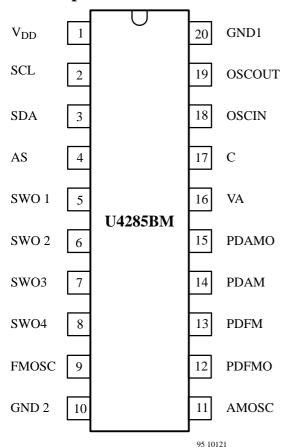
Extended Type Number	Package	Remarks
U4285BM-AFS	SSO20 plastic	
U4285BM-AFSG3	SSO20 plastic	Taping according to IEC-286-3

## **Block Diagram**





#### **Pin Description**



Pin	Symbol	Function
1	$V_{DD}$	Supply voltage
2	SCL	I <sup>2</sup> C bus clock
3	SDA	I <sup>2</sup> C bus data
4	AS	Address selection
5	SWO 1	Switching output 1
6	SWO 2	Switching output 2
7	SWO3	Switching output 3
8	SWO4	Switching output 4
9	FMOSC	FM oscillator input
10	GND 2	Ground 2 (analog)
11	AMOSC	AM oscillator input
12	PDFMO	FM analogue output
13	PDFM	FM current output
14	PDAM	AM current output
15	PDAMO	AM analogue output
16	VA	Analogue supply voltage
17	С	Capacitor
18	OSCIN	Oscillator input
19	OSCOUT	Oscillator output
20	GND1	Ground 1 (digital)

### **Functional Description**

The U4285BM is controlled via the 2-wire I<sup>2</sup>C bus. For programming there are one module address byte, two subaddress bytes and five data bytes.

The module address contains a programmable address bit A 1 which with address select input AS (Pin 4) makes it possible to operate two U4285BM in one system. If bit A 1 is identical with the status of the address select input AS, the chip is selected .

The subaddress determines which one of the data bytes is transmitted first. If subaddress of R-divider is transmitted, the sequence of the next data bytes is DB 0 (Status), DB 1 and DB 2.

If subaddress of N-divider is transmitted, the sequence of the next data bytes is DB 3 and DB 4. The bit organisation of the module address, subaddress and 5 data bytes are shown in figure 2.

Each transmission on the  $I^2C$  bus begins with the "START"- condition and has to be ended by the "STOP"-condition (see figure 3).

The integrated circuit U4285BM has two separate inputs for AM and FM oscillator. Pre-amplified AM and FM signals are fed to the 16 bit N-divider via AM/FM switch. AM/FM switch is controlled by software. Tuning steps can be selected by 16 bit R-divider. Further there is a digital memory phase detector. There are two separate current sources for AM and FM amplifier (charge pump) as given in electrical characterisitics. It allows independent adjustment of gain, whereby providing high current for high speed tuning and low current for stable tuning.



# **Bit Organization**

	MSB							LSB
Module address	1	1	0	0	1	0	0/1	0
	A7	A6	A5	A4	A3	A2	A1	A0
Subaddress (R-divider)	X	X	X	0	0	1	X	X
Subaddress (N-divider)	X	X	X	X	1	1	X	X
	MSB							LSB
Data byte 0 (Status)	SWO1	SWO2	SWO3	SWO4	AM/ FM	PD ANA	PD POL	PD CUR
	D7	D6	D5	D4	D3	D2	D1	D0
Data byte 1	215			R-di	vider			28
		•						
Data byte 2	27			R-di	vider			20
		•						•
Data byte 3	215	N-divider					28	
Data byte 4	27	N-divider						20

	LOW	HIGH
AM/FM	FM-operation	AM-operation
PD – ANA	PD analog	TEST
PD – POL	Negative polarity	Positive polarity
PD – CUR	Output current 2	Output current 1

Figure 2.

# **U4285BM**



### **Transmission Protocol**

	MSB L	SB										
S	Address	A	A	Subaddress	A	Data 0	A	Data 1	A	Data 2	A	P
	A7	A0		R-divider								i l

	MSB I	LSB								
S	Address		Α	Subaddress	A	Data 3	A	Data 4	A	P
	A7	A0		N-divider				A		

S = Start P = Stop A = Acknowledge

Figure 3.

# **Absolute Maximum Ratings**

Par	rameters	Symbol	Value	Unit
Supply voltage	Pin 1	V <sub>DD</sub>	-0.3 to +6	V
Input voltage	Pins 2, 3, 4, 9, 11, 18 and 19	$V_{\rm I}$	$-0.3$ to $V_{DD} + 0.3$	V
Output current	Pins 3, 5, 6, 7 and 8	I <sub>O</sub>	−1 to +5	mA
Output drain voltage	Pins 5, 6, 7 and 8	V <sub>OD</sub>	15	V
Analogue supply voltage with 220 $\Omega$ seriell resistant	Pin 16 ce 2 minutes <sup>1</sup>	$egin{array}{c} V_A \ V_A \end{array}$	6 to 15 24	V V
Output current	Pins 12 and 15	$I_{AO}$	−1 to +20	mA
Ambient temperature range	2	T <sub>amb</sub>	-30 to +85	°C
Storage temperature range		T <sub>stg</sub>	-40 to +125	°C
Junction temperature		Tj	125	°C
Electrostatic handling (moderated method 3015.7: all supply		± V <sub>ESD</sub>	1000	V

corresponding our application circuit (page 8)

### **Thermal Resistance**

Parameters	Symbol	Value	Unit
Junction ambient	$R_{thJA}$	160	K/W



### **Electrical Characteristics**

 $V_{DD}$  = 5 V,  $V_A$  = 10 V,  $T_{amb}$  = 25°C, unless otherwise specified

Parameters	Test conditions /	Pin	Symbol	Min.	Тур.	Max.	Unit
Supply voltage		Pin 1	$V_{\mathrm{DD}}$	4.5	5.0	5.5	V
Quiescent supply current	AM-mode	Pin 1	I <sub>DD</sub>		4.0	7.0	mA
	FM-mode		22		4.0	7.0	
FM input sensitivity, $R_G =$	50 Ω FMOSC						
$f_i = 70 \text{ to } 120 \text{ MHz}$		Pin 9	V <sub>SFM</sub>	40			$mV_{rms}$
$f_i = 160 \text{ MHz}$		Pin 9	V <sub>SFM</sub>	150			$mV_{rms}$
AM input sensitivity, R <sub>G</sub> =	50 Ω AMOSC						
$f_i = 0.6 \text{ to } 35 \text{ MHz}$		Pin 11	V <sub>SAM</sub>	40			mV <sub>rms</sub>
Oscillator input sensitivity,	$R_G = 50 \Omega OSCIN$					•	•
$f_i = 0.1 \text{ to } 15 \text{ MHz}$		Pin 18	V <sub>SOSC</sub>	100			mV <sub>rms</sub>
Switching output SWO 1, S	SWO 2, SWO 3, SWO	O 4 (ope					
Output voltage	Pins 5, 6, 7						
LOW	$I_L = 1 \text{ mA}$		V <sub>SWOL</sub>		100	400	mV
Output leakage current	Pins 5, 6, 7		_				
HIGH	V5, V6, V7, V8 = 10	) V	I <sub>OHL</sub>			100	nA
Phase detector PDFM							
Output current 1		Pin 13	$\pm I_{PDFM}$	1600	2000	2400	μΑ
Output current 2		Pin 13	$\pm I_{PDFM}$	400	500	600	μΑ
Leakage current		Pin 13	$\pm I_{PDFML}$			20	nA
Phase detector PDAM							
Output current 1		Pin 14	$\pm I_{PDAM}$	160	200	240	μA
Output current 2		Pin 14	$\pm I_{PDAM}$	40	50	60	μΑ
Leakage current		Pin 14	$\pm I_{PDAM}$			20	nA
Analogue autust DDEMO	DDAMO		L				
Analogue output PDFMO,	i e	. 1 15					
Saturation voltage LOW	Pins 12 a $I = 15 \text{ mA}$	na 15	V -		200	400	mV
HIGH	1 – 13 11124		$egin{array}{c} V_{satL} \ V_{satH} \end{array}$	9.5	9.95	400	V
I <sup>2</sup> C bus SCL, SDA, AS			' Satri	7.5	7.75		1
Input voltage	Pins 2, 3	and 4	V <sub>iBUS</sub>				
HIGH	1 1113 2, 3	and +	11803	3.0		$V_{DD}$	V
LOW				0		1.5	V
Output voltage		Pin 3					
Acknowledge LOW	$I_{SDA} = 3 \text{ mA}$		V <sub>O</sub>			0.4	V
Clock frequency		Pin 2	$f_{SCL}$			100	kHz
Rise time SDA, SCL	Pins 2	and 3	t <sub>r</sub>			1	μs
Fall time SDA, SCL	Pins 2	and 3	$t_{\mathrm{f}}$			300	ns
Period of SCL		Pin 2					
HIGH	HIGH		t <sub>H</sub>	4.0			μs
LOW	LOW		$t_{ m L}$	4.7			μs



Parameters	Test conditions / Pin	Symbol	Min.	Тур.	Max.	Unit
Setup time						
Start condition Data Stop condition Time space 1)		$t_{ m sSTA}$ $t_{ m sDAT}$ $t_{ m sSTOP}$ $t_{ m wSTA}$	4.7 250 4.7 4.7			μs ns μs μs
Hold time						
Start condition DATA		t <sub>hSTA</sub> t <sub>hDAT</sub>	4.0 0			μs μs

 $<sup>^{1)}</sup>$  This is a space of time where the bus must be free from data transmission and before a new transmission can be started

# **Bus Timing**

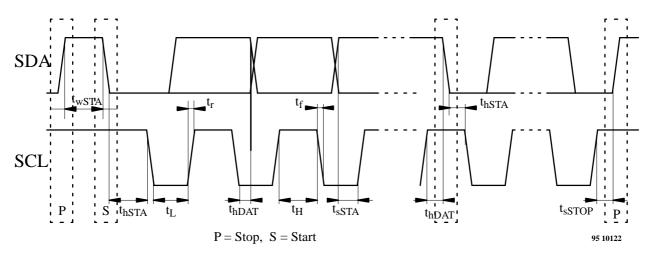


Figure 4.

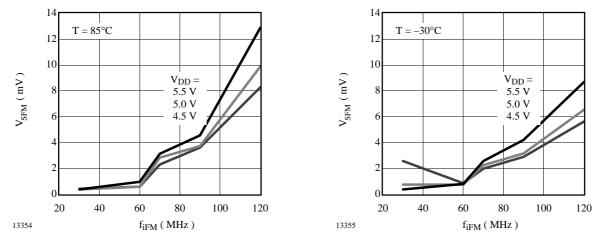


Figure 5. FM input sensitivity

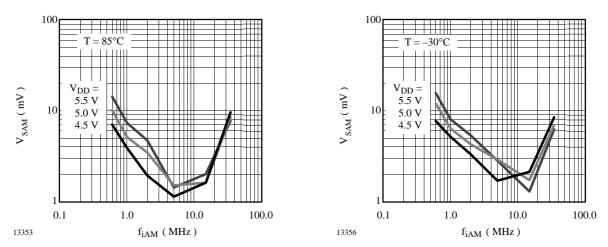


Figure 6. AM input sensitivity

### **Application Circuit**

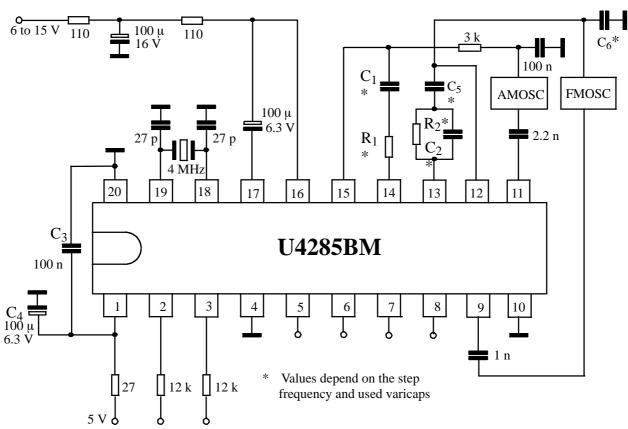


Figure 7.

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#### **Recommendations for Applications**

- $C_3 = 100 \text{ nF}$  should be very close to Pin 1 ( $V_{DD}$ ) and Pin 20 (GND 1)
- GND 2 (Pin 10 analogue ground) and GND 1
   (Pin 20 digital ground) must be connected according to figure 8
- 4 MHz crystal must be very close to Pin 18 and Pin 19
- Components of the charge pump (C<sub>1</sub>/R<sub>1</sub> for AM and C<sub>2</sub>/R<sub>2</sub> for FM) should be very close to Pin 14 with respect to Pin 13.

### **PCB-Layout**

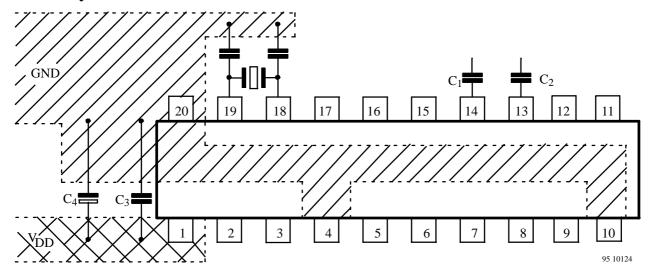
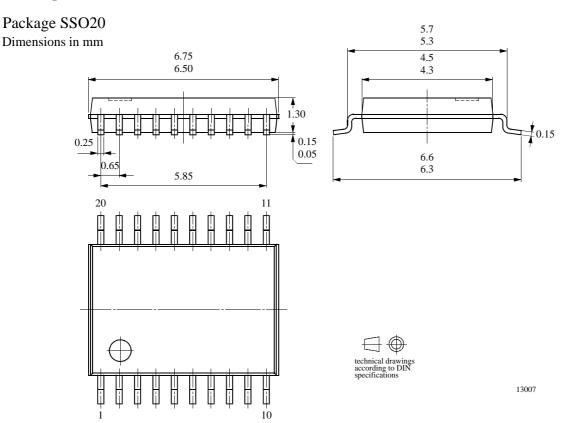


Figure 8.



# **Package Information**



# **U4285BM**



#### **Ozone Depleting Substances Policy Statement**

It is the policy of TEMIC TELEFUNKEN microelectronic GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**TEMIC TELEFUNKEN microelectronic GmbH** semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**TEMIC** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

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